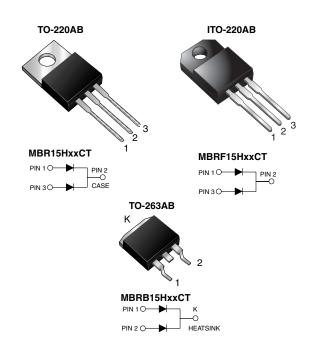


New Product MBR(F,B)15H35CT thru MBR(F,B)15H60CT

Vishay General Semiconductor

Dual Common-Cathode Schottky Rectifier

High Barrier Technology for Improved High Temperature Performance



PRIMARY CHARACTERISTICS					
I _{F(AV)}	7.5 A x 2				
V _{RRM}	35 V to 60 V				
I _{FSM}	150 A				
V_{F}	0.55 V, 0.61 V				
I _R	50 μΑ				
T _J max.	175 °C				

FEATURES

- Guardring for overvoltage protection
- Lower power losses, high efficiency
- Low forward voltage drop
- · Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T _C = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	MBR15H35CT	MBR15H45CT	MBR15H50CT	MBR15H60CT	UNIT	
Maximum repetitive peak reverse voltage	V_{RRM}	35	45	50	60	V	
Working peak reverse voltage	V_{RWM}	35	45	50	60	V	
Maximum DC blocking voltage	V_{DC}	35	45	50	60	V	
Max. average forward rectified current total device (Fig. 1) per diode	I _{F(AV)}	15 7.5				Α	
Non-repetitive avalanche energy per diode at 25 °C, I _{AS} = 4 A, L = 10 mH	E _{AS}	80			mJ		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	150			Α		
Peak repetitive reverse surge current per diode at t_p = 2.0 μ s, 1 kHz	I _{RRM}	1.0 0.5			А		
Peak non-repetitive reverse energy (8/20 µs waveform)	E _{RSM}	20 10			mJ		

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MAXIMUM RATINGS (T _C = 25 °C unless otherwise noted)								
PARAMETER	SYMBOL	MBR15H35CT MBR15H45CT MBR15H50CT MBR15H60CT						
Electrostatic discharge capacitor voltage human body model: C = 100 F, R = 1.5 k Ω	V _C	25				kV		
Voltage rate of change (rated V _R)	dV/dt	10 000 V				V/µs		
Operating junction temperature range	TJ	- 65 to + 175			°C			
Storage temperature range	T _{STG}	- 65 to + 175			°C			
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min	V _{AC}	1500			V			

ELECTRICAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)								
PARAMETER	TEST CONDITIONS		SYMBOL	MBR15H35CT MBR15H45CT		MBR15H50CT MBR15H60CT		UNIT
				TYP.	MAX.	TYP.	MAX.	
Maximum instantaneous forward voltage per diode ⁽¹⁾	$I_F = 7.5 \text{ A}$ $I_F = 7.5 \text{ A}$ $I_F = 15 \text{ A}$ $I_F = 15 \text{ A}$		V _F	- 0.50 - 0.61	0.63 0.55 0.75 0.66	- 0.58 - 0.68	0.73 0.61 0.87 0.72	>
Maximum reverse current at rated V _R per diode ⁽²⁾		T _J = 25 °C T _J = 125 °C	I _R	3.0	50 10	2.0	50 10	μA mA

Notes

(1) Pulse test: 300 μ s pulse width, 1 % duty cycle

(2) Pulse test: Pulse width \leq 40 ms

THERMAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)						
PARAMETER SYMBOL MBR MBRF MBRB UN						
Maximum thermal resistance per diode	$R_{ heta JC}$	3.0	5.0	3.0	°C/W	

ORDERING INFORMATION (Example)								
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE			
TO-220AB	MBR15H45CT-E3/45	1.85	45	50/tube	Tube			
ITO-220AB	MBRF15H45CT-E3/45	1.99	45	50/tube	Tube			
TO-263AB	MBRB15H45CT-E3/45	1.35	45	50/tube	Tube			
TO-263AB	MBRB15H45CT-E3/81	1.35	81	800/reel	Tape and reel			
TO-220AB	MBR15H45CTHE3/45 (1)	1.85	45	50/tube	Tube			
ITO-220AB	MBRF15H45CTHE3/45 (1)	1.99	45	50/tube	Tube			
TO-263AB	MBRB15H45CTHE3/45 (1)	1.35	45	50/tube	Tube			
TO-263AB	MBRB15H45CTHE3/81 (1)	1.35	81	800/reel	Tape and reel			

Note:

(1) Automotive grade AEC Q101 qualified



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RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

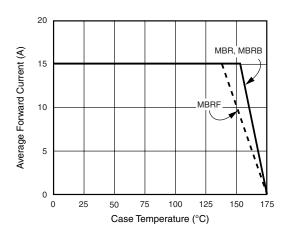


Figure 1. Forward Derating Curve Per Diode

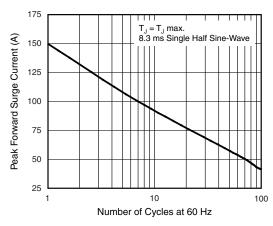


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

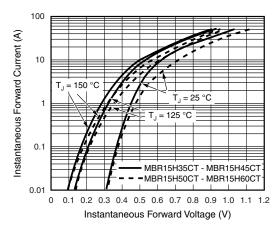


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

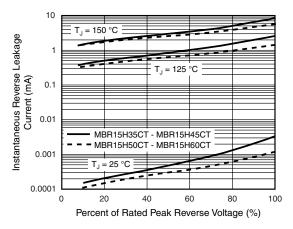


Figure 4. Typical Reverse Characteristics Per Diode

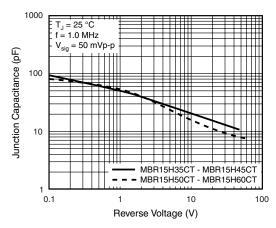


Figure 5. Typical Junction Capacitance Per Diode

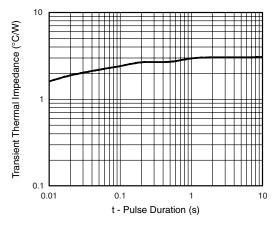


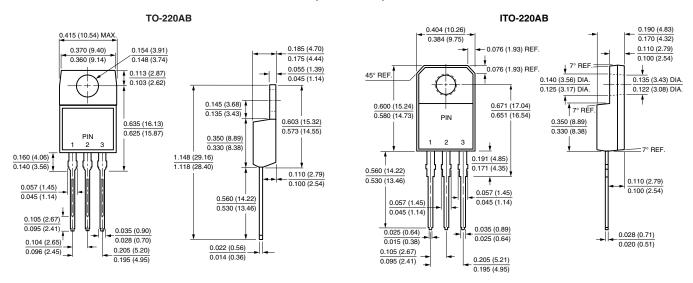
Figure 6. Typical Transient Thermal Impedance Per Diode

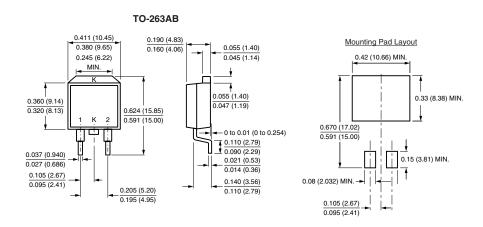
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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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